

**In the claims:**

1-41 (canceled)

42. (currently amended) A semiconductor wafer which comprises:

a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; each of said integrated circuits including:

a centrally disposed core region;

at least one bond pad disposed between said core region and said scribe region;

~~an~~ at least one electrostatic discharge device disposed between one said bond pad and extending at least partially beneath said bond pad; and

an I/O buffer extending unimpeded from ~~disposed between~~ said scribe region and to said core region and disposed laterally of said bond pad and said electrostatic discharge device relative to said core region and said scribe region.

43. (currently amended) A semiconductor The wafer of claim 42, wherein which comprises:

~~a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; each of said integrated circuits including:~~

~~a centrally disposed core region;~~

~~at least one bond pad disposed between said core region and said scribe region;~~

~~an~~ said electrostatic discharge device is disposed at least partially beneath said bond pad; and

~~an I/O buffer disposed between said scribe region and said core region.~~

44-48 (canceled)

49. (currently amended) A method of fabricating a semiconductor wafer which comprises the steps of:

providing a plurality of integrated circuits, each of said integrated circuits separated from the other of said integrated circuits by a scribe region at the periphery of each said integrated circuit; and providing in each of said integrated circuits:

a centrally disposed core region;

at least one bond pad disposed between said core region and said scribe region;

~~an~~ at least one electrostatic discharge device disposed between one said bond pad and extending at least partially beneath said bond pad; and

an I/O buffer extending unimpeded from ~~disposed between~~ said scribe region ~~and to said core region and disposed laterally of said bond pad and said electrostatic discharge device relative to said core region and said scribe region.~~

50-53 (canceled)